



ON Semiconductor®

FDD8447L-F085

N-Channel PowerTrench® MOSFET

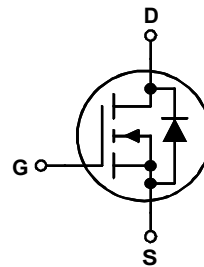
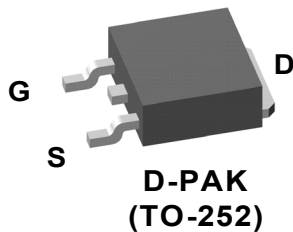
40V, 50A, 11.0mΩ

Features

- Typ $r_{DS(on)}$ = 7.0mΩ at V_{GS} = 10V, I_D = 14A
- Typ $r_{DS(on)}$ = 8.5mΩ at V_{GS} = 4.5V, I_D = 11A
- Fast Switching
- Qualified to AEC Q101
- RoHS Compliant

Applications

- Inverter
- Power Supplies
- Automotive Engine Control
- Power Train Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Primary Switch for 12V and 24V Systems



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage (Note 1)	40	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current Continuous ($T_C < 80^\circ\text{C}$, $V_{GS} = 10\text{V}$)	50	A
	Pulsed	See Figure 4	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	40	mJ
P_D	Power Dissipation	65	W
	Dereate above 25°C	0.43	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to + 175	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Maximum Thermal Resistance Junction to Case	2.3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252, 1in ² copper pad area	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8447L	FDD8447L-F085	D-PAK(TO-252)	13"	12mm	2500 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	1.0	1.9	3.0	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 14\text{A}$, $V_{GS} = 10\text{V}$	-	7.0	8.5	m Ω
		$I_D = 11\text{A}$, $V_{GS} = 4.5\text{V}$	-	8.5	11.0	
		$I_D = 14\text{A}$, $V_{GS} = 10\text{V}$, $T_J = 125^\circ\text{C}$	-	10.4	14.0	
g_{FS}	Forward Transconductance	$I_D = 14\text{A}$, $V_{DS} = 5\text{V}$	-	58	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	-	1970	-	pF	
C _{oss}	Output Capacitance		-	250	-	pF	
C _{rss}	Reverse Transfer Capacitance		-	150	-	pF	
R _g	Gate Resistance	f = 1MHz	-	1.27	-	Ω	
Q _{g(TOT)}	Total Gate Charge at 10V	V _{GS} = 0 to 10V	V _{DD} = 20V I _D = 14A V _{GS} = 10V	-	37	52	nC
Q _{g(5)}	Total Gate Charge at 5V	V _{GS} = 0 to 5V		-	20	28	nC
Q _{gs}	Gate to Source Gate Charge			-	6	-	nC
Q _{gd}	Gate to Drain “Miller” Charge			-	7	-	nC

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 20\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$	-	12	21	ns
t_r	Rise Time		-	12	21	ns
$t_{d(off)}$	Turn-Off Delay Time		-	38	61	ns
t_f	Fall Time		-	9	18	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 14\text{ A}$	-	0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 14\text{ A}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	22	29	ns
Q_{rr}	Reverse Recovery Charge		-	11	14	nC

Notes:1: Starting $T_J = 25^\circ\text{C}$ to 175°C .2: Starting $T_J = 25^\circ\text{C}$, $L = 0.05\text{ mH}$, $I_{AS} = 40\text{ A}$

Typical Characteristics

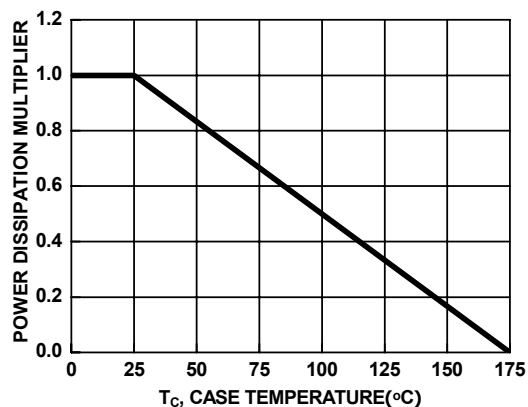


Figure 1. Normalized Power Dissipation vs Case Temperature

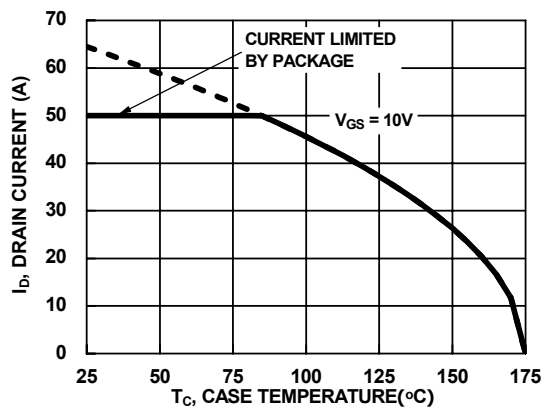


Figure 2. Maximum Continuous Drain Current vs Case Temperature

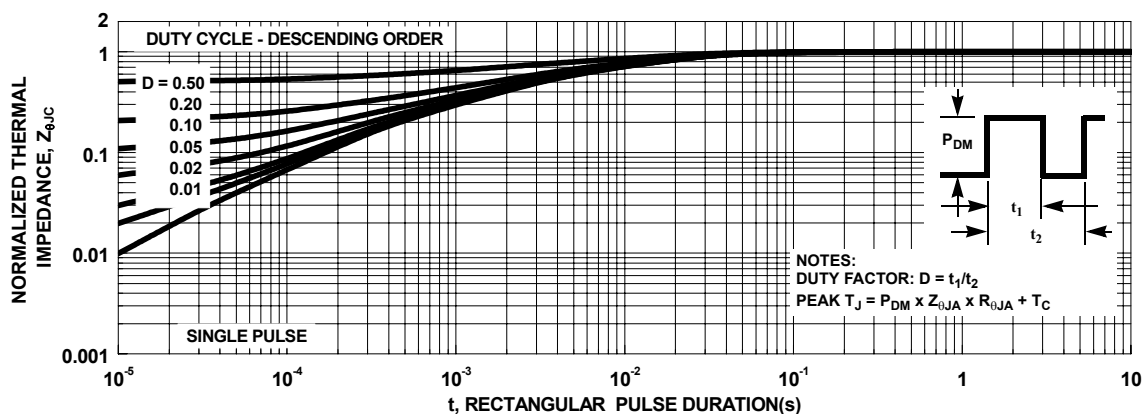


Figure 3. Normalized Maximum Transient Thermal Impedance

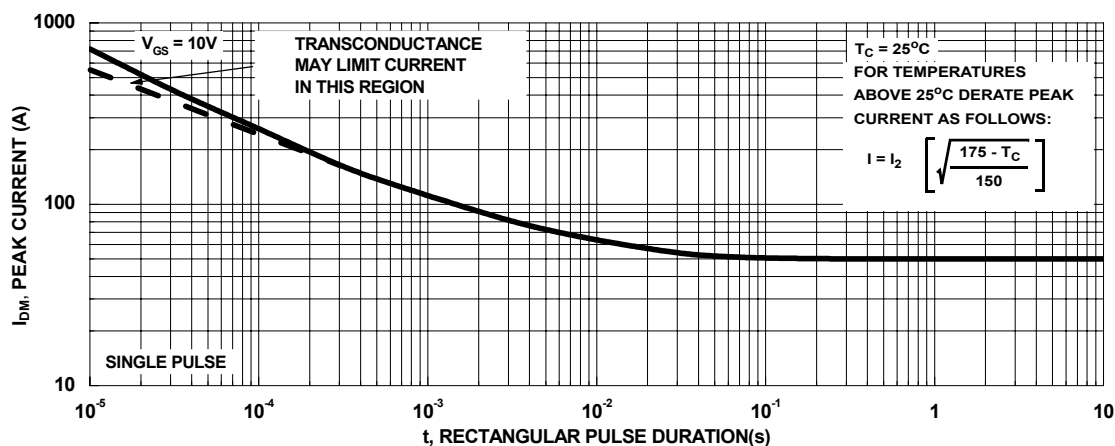


Figure 4. Peak Current Capability

Typical Characteristics

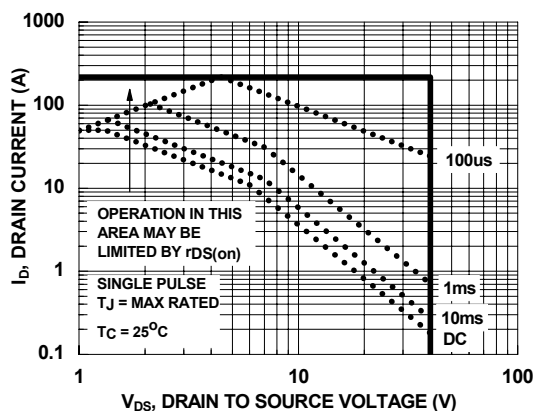


Figure 5. Forward Bias Safe Operating Area

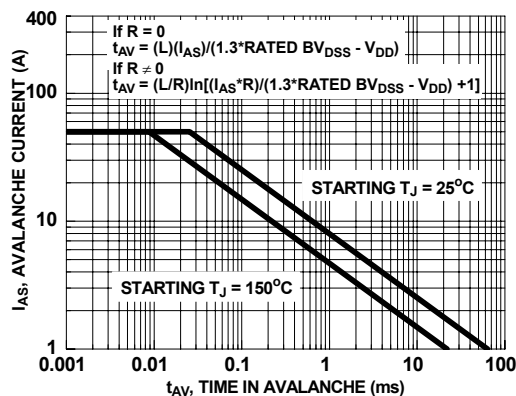


Figure 6. Unclamped Inductive Switching Capability

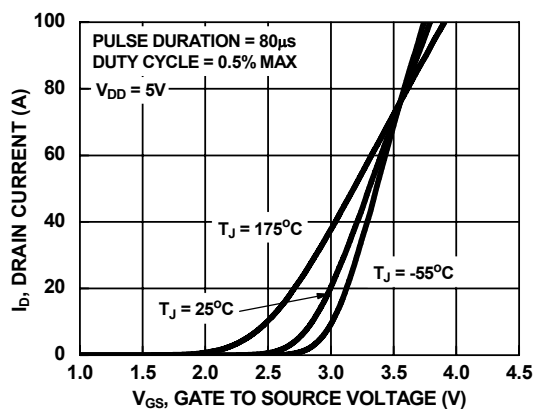


Figure 7. Transfer Characteristics

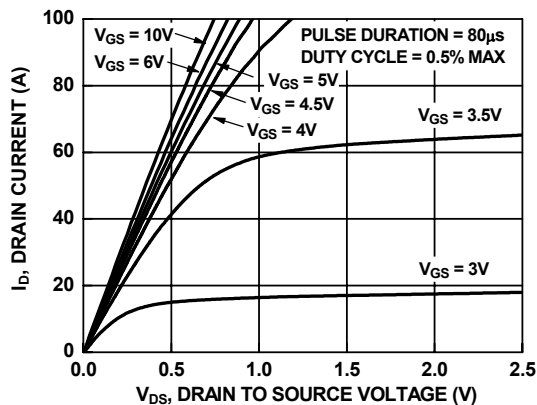


Figure 8. Saturation Characteristics

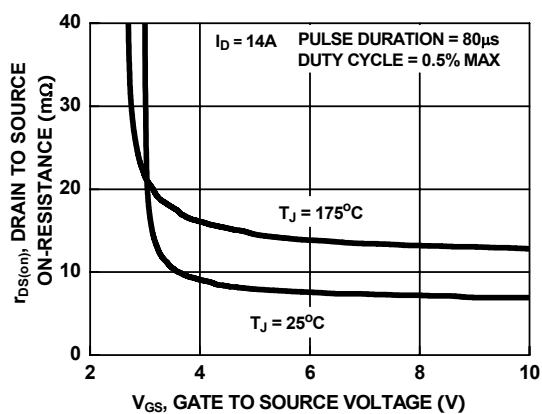


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

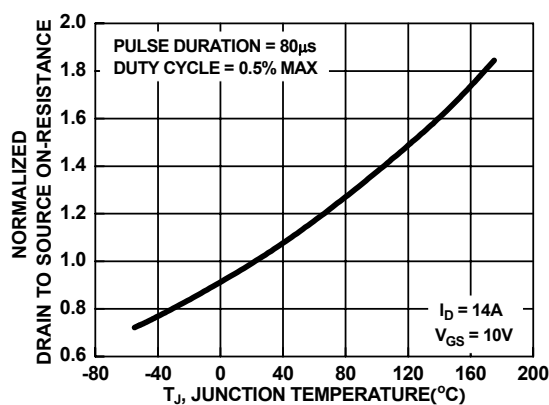


Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature

Typical Characteristics

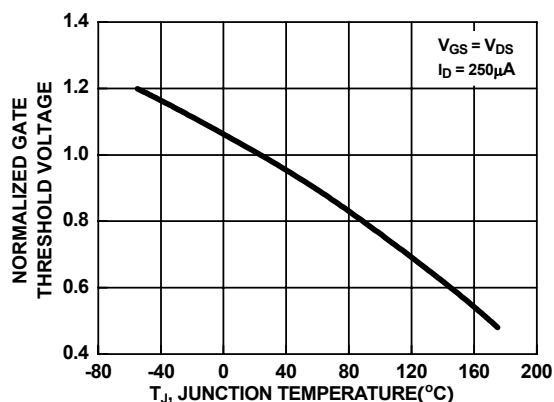


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

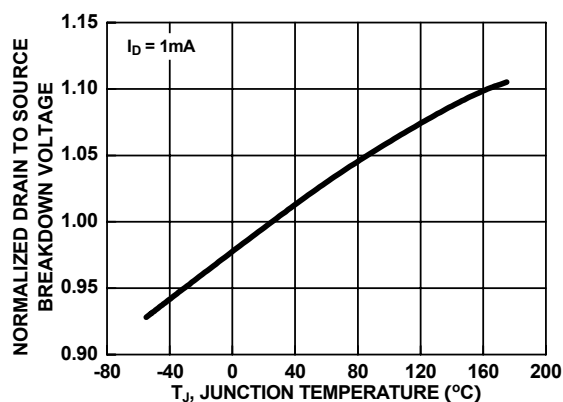


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

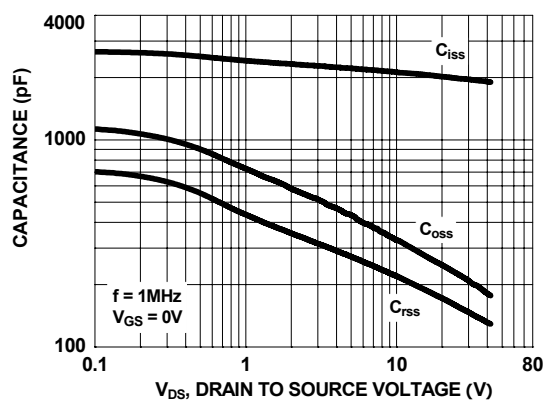


Figure 13. Capacitance vs Drain to Source Voltage

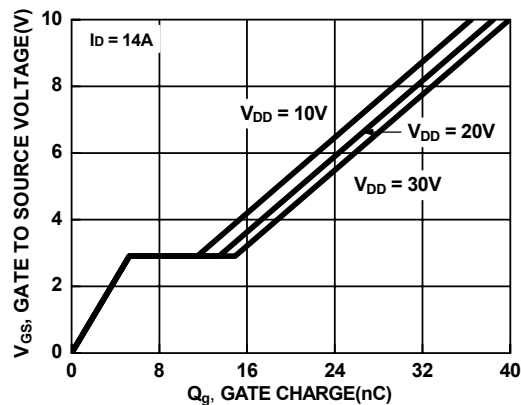


Figure 14. Gate Charge vs Gate to Source Voltage

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